

ABSTRACT OF THE DISCLOSURE

A semiconductor chip comprises a base substrate, a bulk device region having a bulk growth layer on a part of the base substrate, an SOI device region having a buried insulator on the base substrate and a silicon layer on the buried insulator, and a boundary layer located at the boundary between the bulk device region and the SOI device region. The bulk device region has a first device-fabrication surface in which a bulk device is positioned on the bulk growth layer. The SOI device region has a second device-fabrication surface in which an SOI device is positioned on the silicon layer. The first and second device-fabrication surfaces are positioned at a substantially uniform level.